NCE2321A

NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE2321A uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications.

General Features

• $V_{DS} = -20V, I_{D} = -4.5A$

 $R_{DS(ON)}$ <70m Ω @ V_{GS} =-1.8V

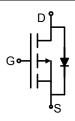
 $R_{DS(ON)}$ <50m Ω @ V_{GS} =-2.5V

 $R_{DS(ON)}$ < 40m Ω @ V_{GS} =-4.5V

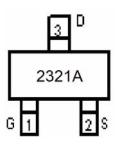
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

Application

- PA switch
- Load switch
- Power management



Schematic diagram



Marking and pin assignment



SOT-23 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2321A	NCE2321A	SOT-23	Ø180mm	8 mm	3000 units

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	-20	V	
Gate-Source Voltage	V _{GS}	±12	V	
Drain Current -Continuous	I _D	-4.5	Α	
Drain Current -Pulsed (Note 1)	I _{DM}	-20	Α	
Maximum Power Dissipation	P _D	1.7	W	
Operating Junction and Storage Temperature Range	T_{J}, T_{STG}	-55 To 150	°C	

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	73.5	°C/W
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NCE2321A

Electrical Characteristics (T_A =25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	•			•		
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V,V _{GS} =0V	-	-	-1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	•			•		
Gate Threshold Voltage	$V_{GS(th)}$	V _{DS} =V _{GS} ,I _D =-250μA	-0.45	-0.6	-1.0	V
	R _{DS(ON)}	V _{GS} =-4.5V, I _D =-4 A	-	31	40	
Drain-Source On-State Resistance		V _{GS} =-2.5V, I _D =-2A	-	37	50	mΩ
		V _{GS} =-1.8V, I _D =-1A		47	70	
Forward Transconductance	g FS	V _{DS} =-5V,I _D =-4A	-	13	-	S
Dynamic Characteristics (Note4)	-					
Input Capacitance	C _{lss}	15)()(0)(-	1159	-	PF
Output Capacitance	Coss	V_{DS} =-15V, V_{GS} =0V,	-	133	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	118	-	PF
Switching Characteristics (Note 4)		,		·		
Turn-on Delay Time	t _{d(on)}		-	23	-	nS
Turn-on Rise Time	t _r	V_{DD} =-10V, I_{D} =-3.2A ,	-	25	-	nS
Turn-Off Delay Time	t _{d(off)}	R_L =2.2 Ω , V_{GS} =-4.5 V , R_g =1 Ω	-	55	-	nS
Turn-Off Fall Time	t _f		-	13	-	nS
Total Gate Charge	Qg		-	14.5	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =-10V,I _D =-4A,V _{GS} =-4.5V	-	2.2	-	nC
Gate-Drain Charge	Q_{gd}		-	2.5	-	nC
Drain-Source Diode Characteristics	1	<u>'</u>	ı	1		1
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-5.3A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-5.3	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width $\leq 300 \mu$ s, Duty Cycle $\leq 2\%$.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

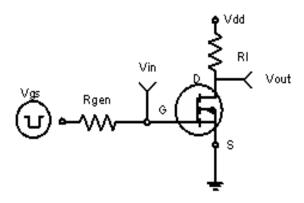


Figure 1:Switching Test Circuit

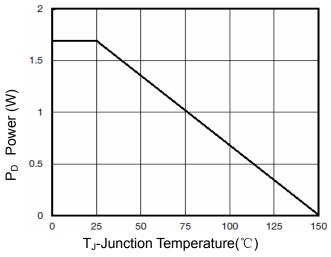


Figure 3 Power Dissipation

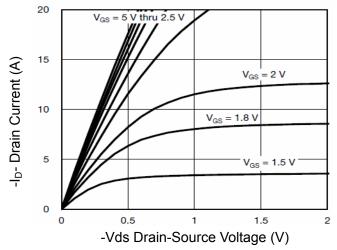


Figure 5 Output Characteristics

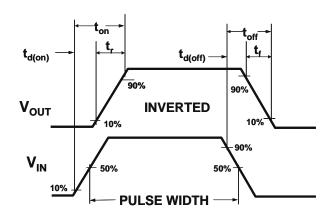


Figure 2:Switching Waveforms

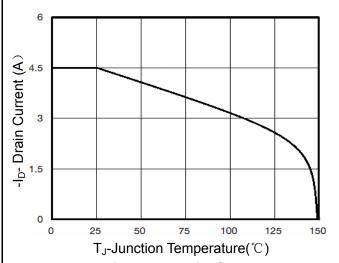


Figure 4 Drain Current

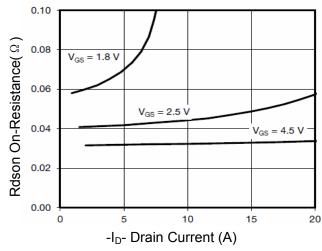
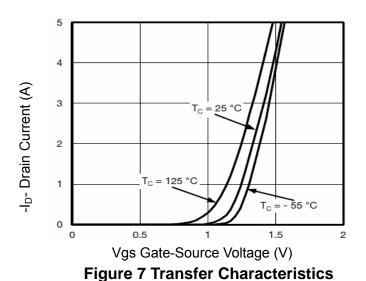


Figure 6 Drain-Source On-Resistance





O 0.08
O 0.08
O 0.08
T_J = 125 °C
T_J = 25 °C

Figure 9 Rdson vs Vgs

-Vgs Gate-Source Voltage (V)

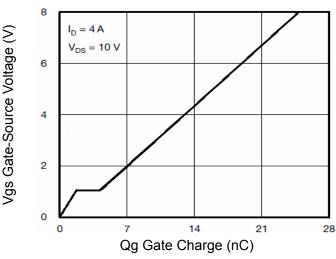


Figure 11 Gate Charge

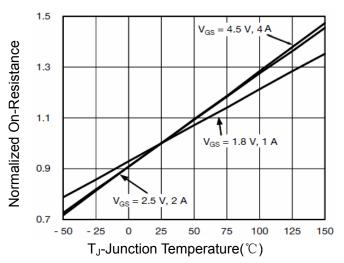


Figure 8 Drain-Source On-Resistance

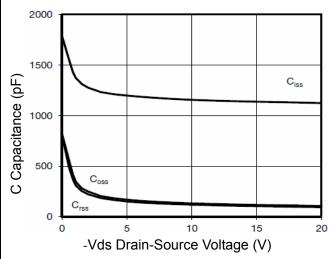


Figure 10 Capacitance vs Vds

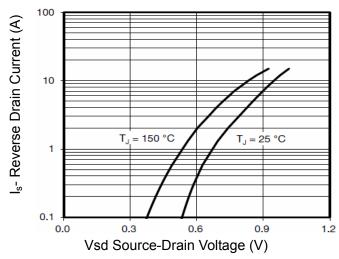


Figure 12 Source- Drain Diode Forward



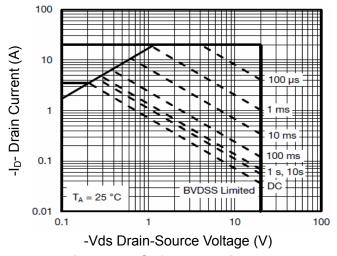


Figure 13 Safe Operation Area

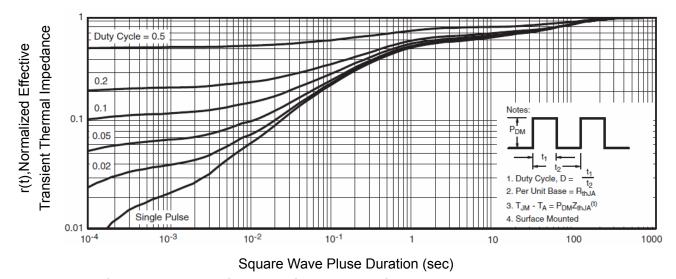
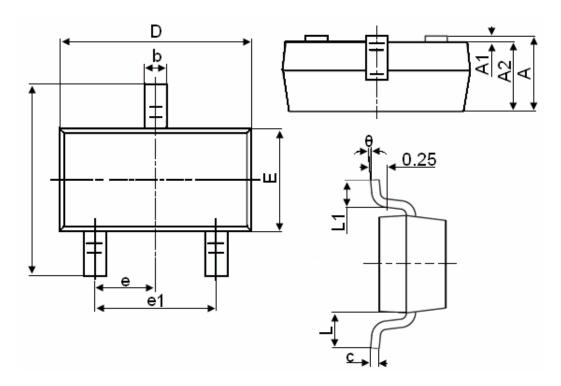


Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Information



Symbol	Dimensions in Millimeters				
	MIN.	MAX.			
Α	0.900	1.150			
A1	0.000	0.100			
A2	0.900	1.050			
b	0.300	0.500			
С	0.080	0.150			
D	2.800	3.000			
E	1.200	1.400			
E1	2.250	2.550			
е	0.950TYP				
e1	1.800	2.000			
L	0.550REF				
L1	0.300	0.500			
θ	0°	8°			

Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- $5. \ Controlling \ dimension \ is \ millimeter, \ converted \ inch \ dimensions \ are \ not \ necessarily \ exact.$



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NCE2321A

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